







TPS3700-Q1 SLVSCI7C - MARCH 2014 - REVISED MARCH 2021

TPS3700-Q1 Automotive High Voltage (18V) Window Voltage Detector With Internal Reference for Over and Undervoltage Monitoring

1 Features

- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
 - Device Temperature Grade 1: –40°C to 125°C Ambient Operating Temperature Range
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C6
- **Functional Safety-Capable**
 - Documentation available to aid functional safety system design
- Wide Supply Voltage Range: 1.8 V to 18 V
- Adjustable Threshold: Down to 400 mV
- Open-Drain Outputs for Overvoltage and **Undervoltage Detection**
- Low Quiescent Current: 5.5 µA (typ)
- High Threshold Accuracy:
 - 1% Over Temperature
 - 0.25% (typ)
- Internal Hysteresis: 5.5 mV (typ)
- Available in ThinSOT23-6 and WSON Packages

2 Applications

- Advanced Driver Assistance System (ADAS)
- **ADAS Domain Controller**
- Digital cockpit
- **Automotive Infotainment & Cluster**
- HEV/EV OBC and wireless charger
- **Industrial Robot**

3 Description

TPS3700-Q1 wide-supply window voltage detector operates over a 1.8 V to 18 V range. The device has two high-accuracy comparators with an internal 400-mV reference and two open-drain outputs rated to 18 V for overvoltage and undervoltage detection. The TPS3700-Q1 device can be used as a window voltage detector or as two independent voltage monitors; the monitored voltage can be set with the use of external resistors. For even wider input voltage capability up to 65 V, see the TPS37A-Q1 or the TPS38A-Q1 devices.

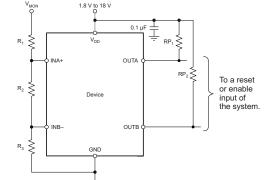
The OUTA terminal is driven low when the voltage at the INA+ terminal drops below $(V_{\text{IT+}}-V_{\text{hys}})$, and goes high when the voltage returns above the respective threshold (V_{IT+}). The OUTB terminal is driven low when the voltage at the INB- terminal rises above V_{IT+}, and goes high when the voltage drops below the respective threshold $(V_{IT+} - V_{hvs})$. Both comparators in the TPS3700-Q1 device include built-in hysteresis for filtering to reject brief glitches, thereby ensuring stable output operation without false triggering.

The TPS3700-Q1 device is available in a Thin SOT-6 and a 1.5-mm x 1.5-mm WSON-6 package and is specified over the junction temperature range of -40°C to 125°C.

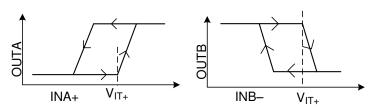
Device Information

ORDER NUMBER	PACKAGE (1)	BODY SIZE		
TPS3700-Q1	SOT23 (6)	2.90 mm × 1.60 mm		
1F33700-Q1	WSON (6)	1.50 mm x 1.50 mm		

For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Schematic



Output vs Input Thresholds and Hysteresis



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Changed device status from Product Preview to Production Data.



5 Pin Configuration and Functions

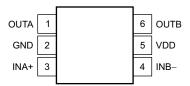


Figure 5-1. DDC Package SOT-6 Top View

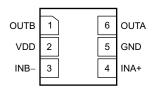


Figure 5-2. DSE Package WSON-6 Top View

Table 5-1. Pin Functions

	PIN		1/0	DESCRIPTION
NAME	NAME DDC DSE		1/0	DESCRIPTION
GND	2	5	_	Ground
INA+	3	4	I	This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this terminal drops below the threshold voltage ($V_{\rm IT+} - V_{\rm HYS}$), OUTA is driven low.
INB-	4	3	I	This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this terminal exceeds the threshold voltage (V_{IT+}), OUTB is driven low.
OUTA	1	6	0	INA+ comparator open-drain output. OUTA is driven low when the voltage at this comparator is below ($V_{\text{IT+}} - V_{\text{HYS}}$). The output goes high when the sense voltage returns above the respective threshold ($V_{\text{IT+}}$).
OUTB	6	1	0	INB– comparator open-drain output. OUTB is driven low when the voltage at this comparator exceeds $V_{\text{IT+}}$. The output goes high when the sense voltage returns below the respective threshold ($V_{\text{IT+}} - V_{\text{HYS}}$).
VDD	5	2	I	Supply voltage input. Connect a 1.8-V to 18-V supply to VDD to power the device. Good analog design practice is to place a 0.1-μF ceramic capacitor close to this pin.



6 Specifications

6.1 Absolute Maximum Ratings

Over operating temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
	V_{DD}	-0.3	20	V
Voltage ⁽²⁾	OUTA, OUTB	-0.3	20	V
	INA+, INB-	-0.3	7	V
Current	Output terminal current		40	mA
Operating junction temperature, T _J	-40	125	°C	
Storage temperature range, T _{stg}		-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network ground terminal.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrosatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2500	V
V _{ESD}		Charge device model (CDM), per AEC Q100-011	±1000	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

Over operating temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{DD}	Supply voltage		1.8	18	V
VI	Input voltage	INA+, INB-	0	6.5	V
Vo	Output voltage	OUTA, OUTB	0	18	V

6.4 Thermal Information

		TPS3		
	THERMAL METRIC ⁽¹⁾	DDC (SOT)	DSE (WSON)	UNIT
		6 pins	6 pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	174.0	160.7	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	81.5	101.9	
R _{θJB}	Junction-to-board thermal resistance	47.2	68.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	22.0	5.4	- C/VV
Ψ_{JB}	Junction-to-board characterization parameter	46.9	68.6	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: TPS3700-Q1



6.5 Electrical Characteristics

Over the operating temperature range of T_J = -40°C to 125°C, and 1.8 V < V_{DD} < 18 V, unless otherwise noted. Typical values are at T_J = 25°C and V_{DD} = 5 V.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{DD}	Supply voltage range		1.8		18	V
V _(POR)	Power-on reset voltage ⁽¹⁾	V _{OL} max = 0.2 V, I _(OUTA/B) = 15 μA			0.8	V
V	Positive-going input threshold voltage	V _{DD} = 1.8 V	396	400	404	mV
V_{IT+}	Positive-going input threshold voltage	V _{DD} = 18 V	396	400	404	mV
V _{IT} _	Negative-going input threshold voltage	V _{DD} = 1.8 V	387	394.5	400	mV
v _{IT} _	Negative-going input threshold voltage	V _{DD} = 18 V	387	394.5	400	mV
V _{hys}	Hysteresis voltage (hys = V _{IT+} – V _{IT-})			5.5	12	mV
I _(INA+)	Input current (at the INA+ or INB-	V _{DD} = 1.8 V and 18 V, V _I = 6.5 V	-25	1	25	nA
$I_{(INB-)}$	terminal)	V _{DD} = 1.8 V and 18 V, V _I = 0.1 V	-15	1	15	nA
		V _{DD} = 1.3 V, I _O = 0.4 mA			250	mV
V_{OL}	Low-level output voltage	V _{DD} = 1.8 V, I _O = 3 mA			250	mV
		V _{DD} = 5 V, I _O = 5 mA			250	mV
l	Open-drain output leakage-current	V _{DD} = 1.8 V and 18 V, V _O = V _{DD}			400 404 m 94.5 400 m 94.5 400 m 5.5 12 m 1 25 n 1 15 n 250 m 250 m 250 m 300 n 300 n 5.5 11 μ 6 13 μ 7 13 μ 150 450 μ	nA
I _{lkg(OD)}	Ореп-итапт опфиг теакаде-ситтепт	V _{DD} = 1.8 V, V _O = 18 V	= 15 μA	nA		
		V _{DD} = 1.8 V, no load		5.5	11	μΑ
ı	Supply current	V _{DD} = 5 V		6	13	μΑ
I _{DD}	Supply current	V _{DD} = 12 V		6	13	μΑ
		V _{DD} = 18 V		7	13	μA
	Startup delay ⁽²⁾			150	450	μs
UVLO	Undervoltage lockout ⁽⁴⁾	V _{DD} falling	1.3		1.7	V
		I .				

- (1) The lowest supply voltage (V_{DD}) at which output is active; t_{r(VDD)} > 15 µs/V. Below V_(POR), the output cannot be determined.
- (2) During power on, V_{DD} must exceed 1.8 V for 450 μs (max) before the output is in a correct state.
- (3) High-to-low and low-to-high refers to the transition at the input terminals (INA+ and INB-).
- (4) When V_{DD} falls below UVLO, OUTA is driven low and OUTB goes to high impedance. The outputs cannot be determined below V_(POR).



6.6 Timing Requirements

Over operating temperature range (unless otherwise noted)

			MIN	TYP	MAX	UNIT
t _{PHL}	High-to-low propagation delay ⁽³⁾	V_{DD} = 5 V, 10-mV input overdrive, R_P = 10 kΩ, V_{OH} = 0.9 × V_{DD} , V_{OL} = 400 mV See Figure 6-1		18		μs
t _{PLH}	Low-to-high propagation delay ⁽³⁾	V_{DD} = 5 V, 10-mV input overdrive, R_P = 10 kΩ, V_{OH} = 0.9 × V_{DD} , V_{OL} = 400 mV See Figure 6-1		29		μs

6.7 Timing Diagram

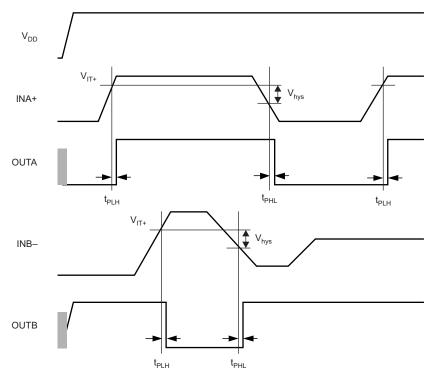


Figure 6-1. Timing Diagram

6.8 Switching Characteristics

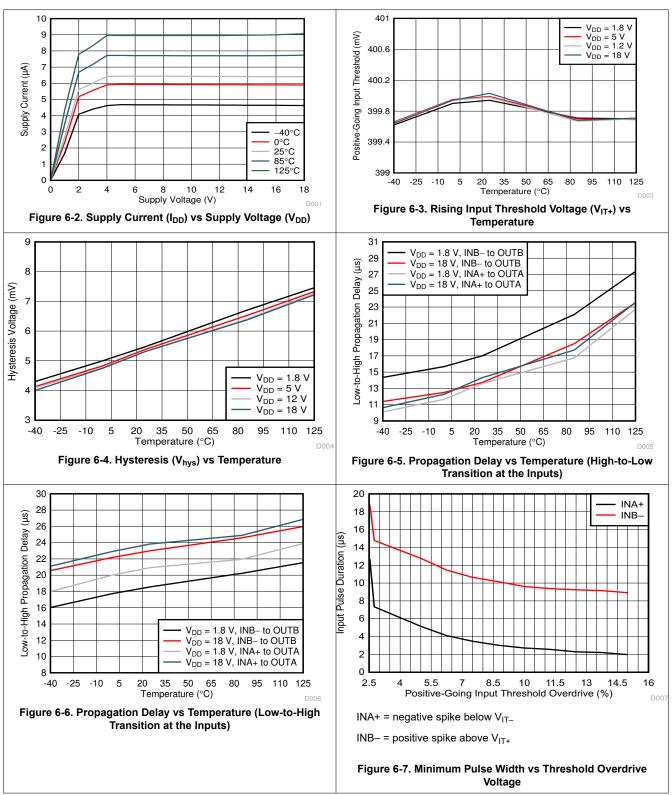
Over operating temperature range (unless otherwise noted)

	PARAMETER	MIN	TYP	MAX	UNIT	
t _r		V_{DD} = 5 V, 10-mV input overdrive, R _P = 10 k Ω , V _O = (0.1 to 0.9) × V _{DD}		2.2		μs
t _f		V_{DD} = 5 V, 10-mV input overdrive, R _P = 10 k Ω , V _O = (0.1 to 0.9) × V _{DD}		0.22		μs

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6.9 Typical Characteristics

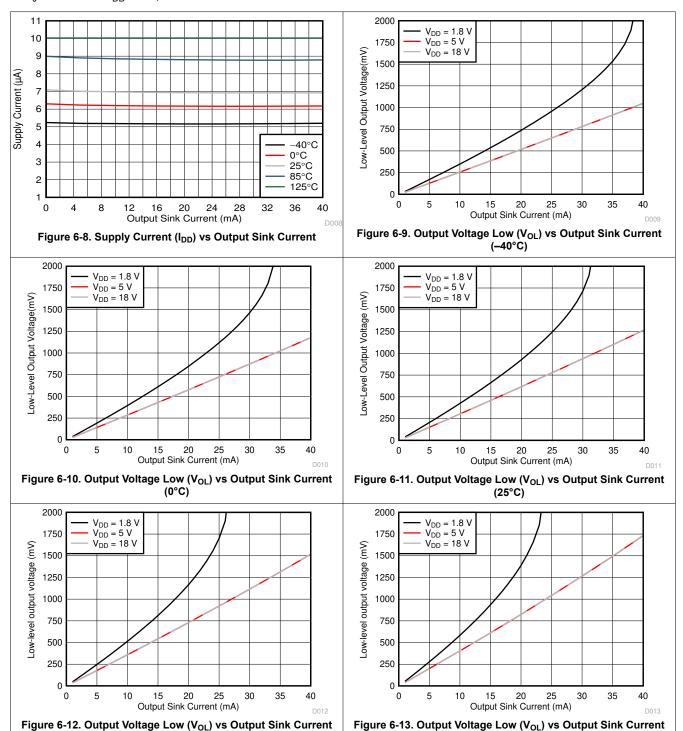
At $T_J = 25$ °C and $V_{DD} = 5$ V, unless otherwise noted.





6.9 Typical Characteristics (continued)

At $T_J = 25$ °C and $V_{DD} = 5$ V, unless otherwise noted.



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(85°C)

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(125°C)

7 Detailed Description

7.1 Overview

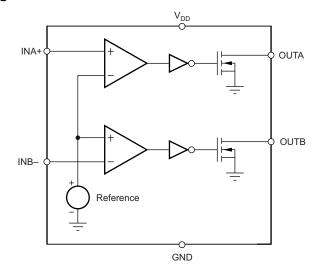
The TPS3700-Q1 device combines two comparators for overvoltage and undervoltage detection. The TPS3700-Q1 device is a wide-supply voltage range (1.8 to 18 V) device with a high-accuracy rising input threshold of 400 mV (1% over temperature) and built-in hysteresis. The outputs are also rated to 18 V and can sink up to 40 mA.

The TPS3700-Q1 device is designed to assert the output signals, as shown in Table 7-1. Each input terminal can be set to monitor any voltage above 0.4 V using an external resistor divider network. With the use of two input terminals of different polarities, the TPS3700-Q1 device forms a window voltage detector. Broad voltage thresholds can be supported that allow the device to be used in a wide array of applications.

	Tubio I II II Gol Go Q I II dili Tubio				
CONDITION	OUTPUT	STATUS			
INA+ > V _{IT+}	NA+ > V _{IT+} OUTA high Output A not asserted				
INA+ < V _{IT}	OUTA low	Output A asserted			
INB > V _{IT+}	OUTB low	Output B asserted			
INB- < V _{IT-}	OUTB high	Output B not asserted			

Table 7-1. TPS3700-Q1 Truth Table

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Inputs (INA+, INB-)

The TPS3700-Q1 device combines two comparators. Each comparator has one external input (inverting and noninverting); the other input is connected to the internal reference. The comparator rising threshold is designed and trimmed to be equal to the reference voltage (400 mV). Both comparators also have a built-in falling hysteresis that makes the device less sensitive to supply rail noise and ensures stable operation.

The INA+ and INB- inputs can swing from ground to 6.5 V, regardless of the device supply voltage used. Although not required in most cases, it is good analog design practice to place a 1-nF to 10-nF bypass capacitor at the comparator input for extremely noisy applications in order to reduce sensitivity to transients and layout parasitics.

For comparator A, the corresponding output (OUTA) is driven to logic low when the input INA+ voltage drops below ($V_{IT+} - V_{hys}$). When the voltage exceeds V_{IT+} , the output (OUTA) goes to a high-impedance state; see Figure 6-1.

For comparator B, the corresponding output (OUTB) is driven to logic low when the voltage at input INB–exceeds V_{IT+} . When the voltage drops below $V_{IT+} - V_{hys}$ the output (OUTB) goes to a high-impedance state;

see Figure 6-1 . Together, these comparators form a window-detection function as discussed in the Section 7.3.3 section.

7.3.2 Outputs (OUTA, OUTB)

In a typical TPS3700-Q1 application, the outputs are connected to a reset or enable input of the processor (such as a digital signal processor [DSP], central processing unit [CPU], field-programmable gate array [FPGA], or application-specific integrated circuit [ASIC]) or the outputs are connected to the enable input of a voltage regulator (such as a DC-DC or low-dropout regulator [LDO]).

The TPS3700-Q1 device provides two open-drain outputs (OUTA and OUTB). Pullup resistors must be used to hold these lines high when the output goes to high impedance (not asserted). By connecting pullup resistors to the proper voltage rails, the outputs can be connected to other devices at the correct interface-voltage levels. The TPS3700-Q1 outputs can be pulled up to 18 V, independent of the device supply voltage. To ensure proper voltage levels, some thought should be given while choosing the pullup resistor values. The pullup resistor value is determined by V_{OL} , sink-current capability, and output-leakage current ($I_{lkg(OD)}$). These values are specified in the Section 6.5 table. By using wired-AND logic, OUTA and OUTB can merge into one logic signal.

Table 7-1 and the Section 7.3.1 section describe how the outputs are asserted or de-asserted. See Figure 6-1 for a timing diagram that describes the relationship between threshold voltages and the respective output.

7.3.3 Window Voltage Detector

The inverting and noninverting configuration of the comparators forms a window voltage detector circuit using a resistor divider network, as shown in Figure 7-1 and Figure 7-2. The input terminals can monitor any system voltage above 400 mV with the use of a resistor divider network. The INA+ and INB- terminals monitor for undervoltage and overvoltage conditions, respectively.

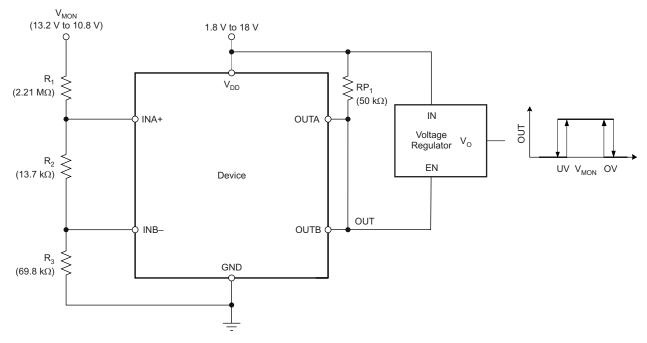


Figure 7-1. Window Voltage Detector Block Diagram

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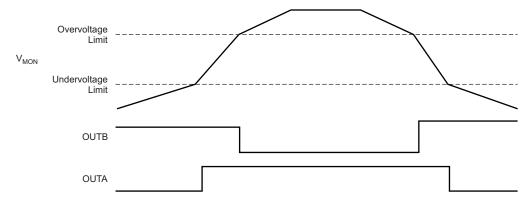


Figure 7-2. Window Voltage Detector Timing Diagram

7.3.4 Immunity to Input Terminal Voltage Transients

The TPS3700-Q1 device is relatively immune to short voltage transient spikes on the input terminals. Sensitivity to transients is dependent on both transient duration and amplitude; see the *Minimum Pulse Width vs Threshold Overdrive Voltage* curve (Figure 6-7) in the Section 6.9 section.

7.4 Device Functional Modes

The TPS3700-Q1 has a single functional mode, which is on when V_{DD} is greater than 1.8 V.

8 Application and Implementation

8.1 Application Information

The TPS3700-Q1 device is a wide-supply voltage window voltage detector that operates over a V_{DD} range of 1.8-V to 18-V. The device has two high-accuracy comparators with an internal 400-mV reference and two open-drain outputs rated to 18 V for overvoltage and undervoltage detection. The device can be used either as a window voltage detector or as two independent voltage monitors. The monitored voltages are set with the use of external resistors.

8.1.1 V_{PULLUP} to a Voltage Other Than V_{DD}

The outputs are often tied to V_{DD} through a resistor. However some applications may require the outputs to be pulled up to a higher or lower voltage than V_{DD} in order to correctly interface with the reset and enable the terminal of other devices.

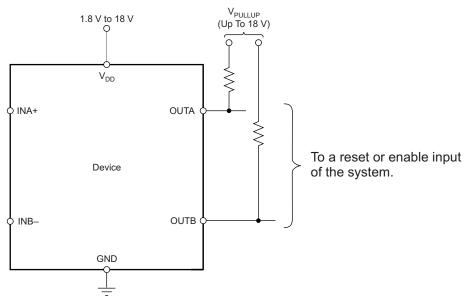


Figure 8-1. Interfacing to Voltages Other Than V_{DD}

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8.1.2 Monitoring V_{DD}

Many applications monitor the same rail that is powering V_{DD} . In these applications the resistor divider is simply connected to the V_{DD} rail.

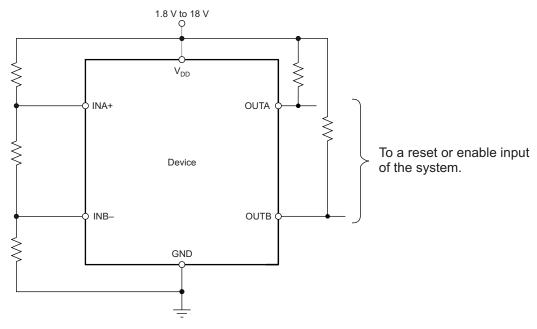
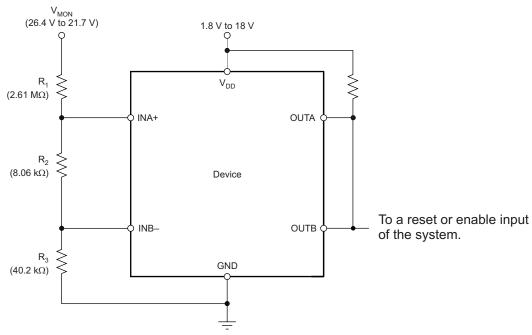


Figure 8-2. Monitoring the Same Voltage as V_{DD}

8.1.3 Monitoring a Voltage Other Than V_{DD}

Some applications monitor rails other than the one that is powering V_{DD} . In these types of applications the resistor divider used to set the desired thresholds in connected to the rail that is being monitored.



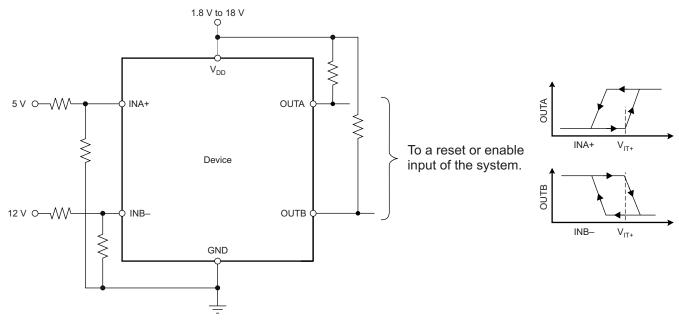
NOTE: The inputs can monitor a voltage higher than V_{DD}max with the use of an external resistor divider network.

Figure 8-3. Monitoring a Voltage Other Than V_{DD}



8.1.4 Monitoring Overvoltage and Undervoltage for Separate Rails

Some applications may want to monitor for overvoltage conditions on one rail while also monitoring for undervoltage conditions on a different rail. In those applications two independent resistor dividers will need to be used.



NOTE: In this case, OUTA is driven low when an undervoltage condition is detected at the 5-V rail and OUTB is driven low when an overvoltage condition is detected at the 12-V rail.

Figure 8-4. Monitoring Overvoltage for One Rail and Undervoltage for a Different Rail



8.2 Typical Application

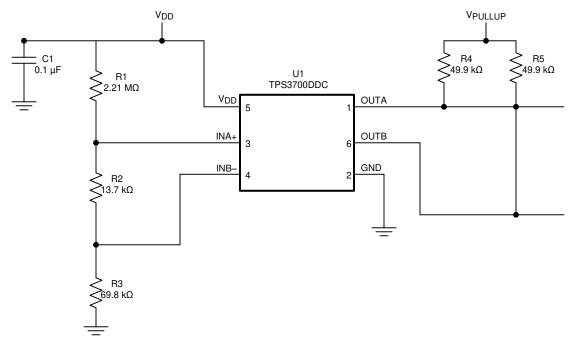


Figure 8-5. Typical Application Schematic

8.2.1 Design Requirements

8.2.1.1 Input Supply Capacitor

Although an input capacitor is not required for stability, connecting a 0.1- μF low equivalent series resistance (ESR) capacitor across the V_{DD} terminal and GND terminal is good analog design practice. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is not located close to the power source.

8.2.1.2 Input Capacitors

Although not required in most cases, for extremely noisy applications, placing a 1-nF to 10-nF bypass capacitor from the comparator inputs (INA+, INB-) to the GND terminal is good analog design practice. This capacitor placement reduces device sensitivity to transients.

8.2.2 Detailed Design Procedure

Use Equation 1 through Equation 4 to calculate the resistor divider values and target threshold voltage.

$$R_T = R_1 + R_2 + R_3$$
 (1)

Select a value for R_T such that the current through the divider is approximately 100-times higher than the input current at the INA+ and INB- terminals. The resistors can have high values to minimize current consumption as a result of low-input bias current without adding significant error to the resistive divider. See the application note *Optimizing Resistor Dividers at a Comparator Input* (SLVA450) for details on sizing input resistors.

Use Equation 2 to calculate the value of R_3 .

$$R_3 = \frac{R_T}{V_{MON(OV)}} \times V_{IT+}$$
 (2)

where

V_{MON(OV)} is the target voltage at which an overvoltage condition is detected



Use Equation 3 or Equation 4 to calculate the value of R₂.

$$R_2 = \left(\frac{R_T}{V_{MON} (no UV)} \times V_{IT+}\right) - R_3$$
(3)

where

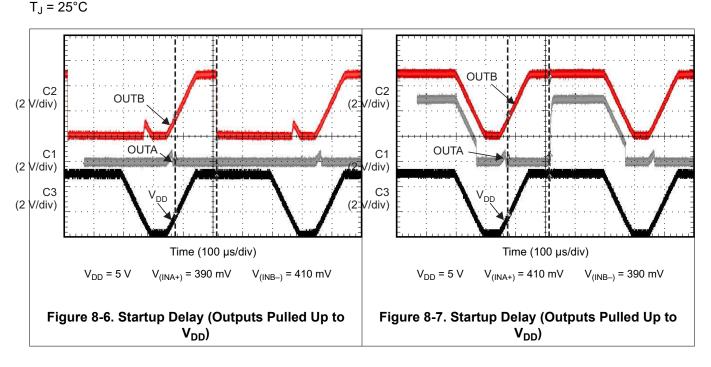
 $V_{MON(no\ UV)}$ is the target voltage at which an undervoltage condition is removed as V_{MON} rises

$$R_2 = \left[\frac{R_T}{V_{MON(UV)}} \times (V_{IT+} - V_{hys}) \right] - R_3$$
(4)

where:

V_{MON(UV)} is the target voltage at which an undervoltage condition is detected

8.2.3 Application Curves



9 Power Supply Recommendations

These devices are designed to operate from an input voltage supply range between 1.8 V and 18 V.



10 Layout

10.1 Layout Guidelines

Placing a 0.1- μ F capacitor close to the V_{DD} terminal to reduce the input impedance to the device is good analog design practice. The pullup resistors can be separated if separate logic functions are needed (see Figure 10-1) or both resistors can be tied to a single pullup resistor if a logical AND function is desired.

10.2 Layout Example

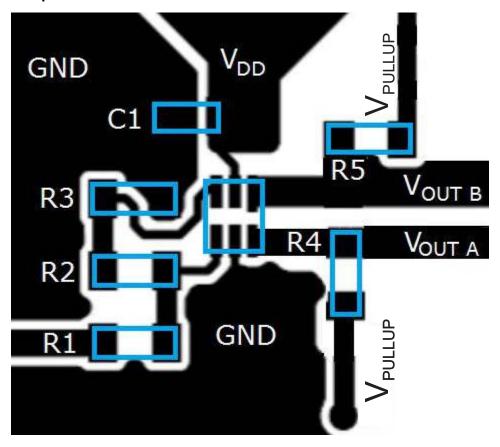


Figure 10-1. TPS3700-Q1 Layout Example



11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- Using the TPS3700 as a Negative Rail Over- and Undervoltage Detector, SLVA600
- Optimizing Resistor Dividers at a Comparator Input, SLVA450
- TPS3700EVM-114 Evaluation Module, SLVU683

11.2 Trademarks

All trademarks are the property of their respective owners.

11.3 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.4 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: TPS3700-Q1



PACKAGE OPTION ADDENDUM

24-Feb-2021

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS3700QDDCRQ1	ACTIVE	SOT-23-THIN	DDC	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	PD7Q	Samples
TPS3700QDSERQ1	ACTIVE	WSON	DSE	6	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	5O	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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24-Feb-2021

OTHER QUALIFIED VERSIONS OF TPS3700-Q1:

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 24-Feb-2021

TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
٧	V	Overall width of the carrier tape
ГР	1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3700QDDCRQ1	SOT- 23-THIN	DDC	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3700QDSERQ1	WSON	DSE	6	3000	179.0	8.4	1.8	1.8	1.0	4.0	8.0	Q2

PACKAGE MATERIALS INFORMATION

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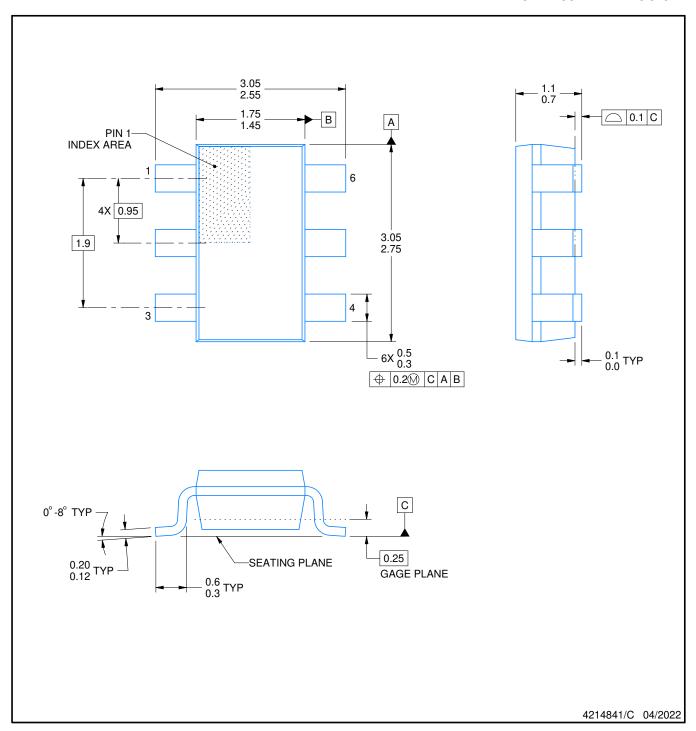


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TPS3700QDDCRQ1	SOT-23-THIN	DDC	6	3000	213.0	191.0	35.0	
TPS3700QDSERQ1	WSON	DSE	6	3000	213.0	191.0	35.0	



SMALL OUTLINE TRANSISTOR

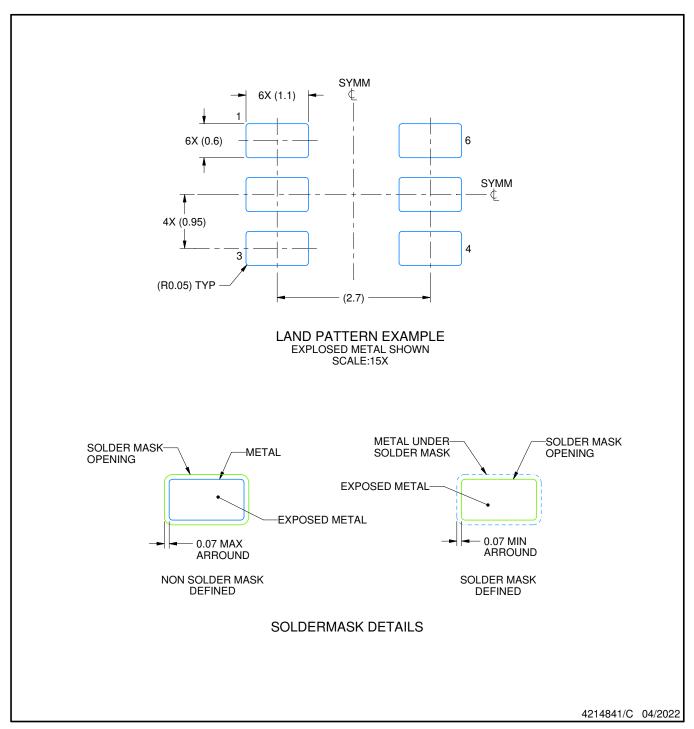


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-193.



SMALL OUTLINE TRANSISTOR

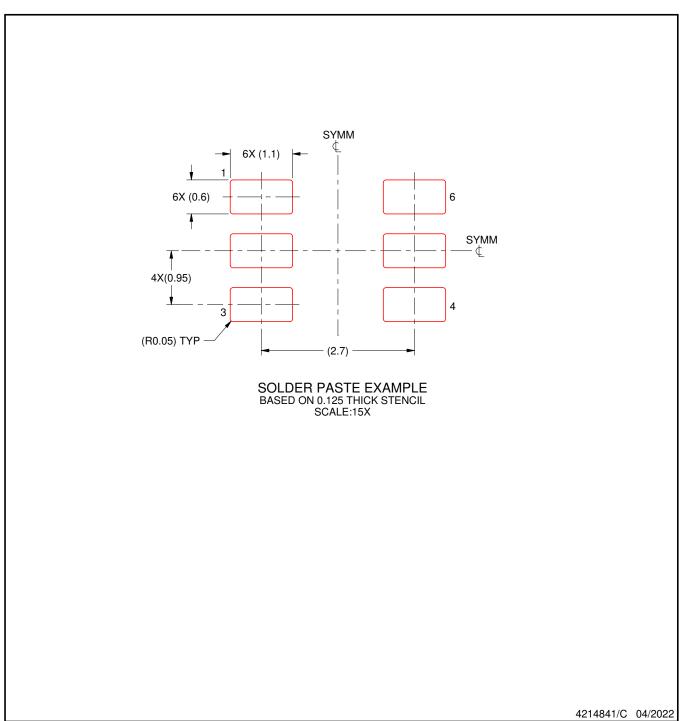


NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR

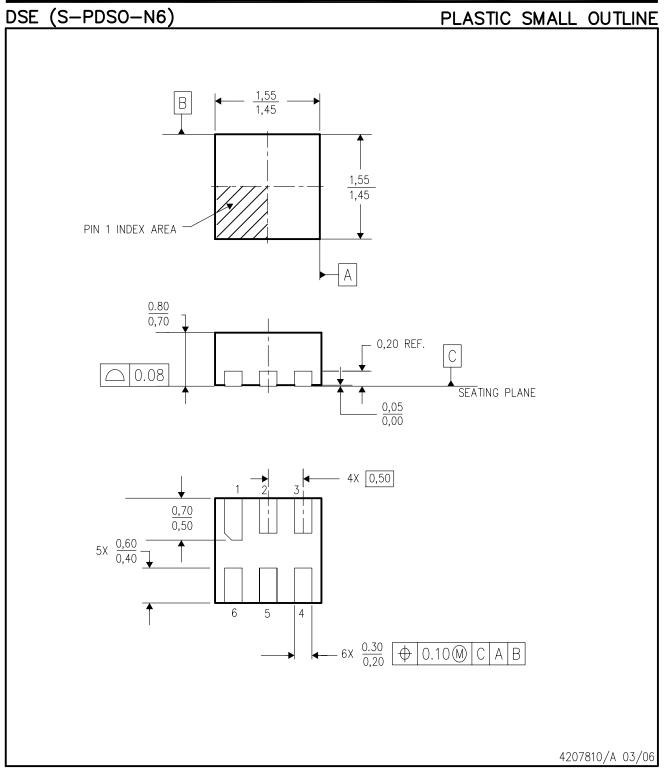


NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

 7. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Small Outline No-Lead (SON) package configuration.
- D. This package is lead-free.



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